



ALPHA & OMEGA
SEMICONDUCTOR



AO4625

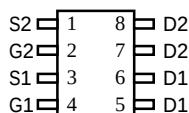
Complementary Enhancement Mode Field Effect Transistor

General Description

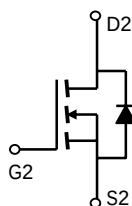
The AO4625 uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in power inverters, and other applications. *Standard Product AO4625 is Pb-free (meets ROHS & Sony 259 specifications). AO4625L is a Green Product ordering option. AO4625 and AO4625L are electrically identical.*

Features

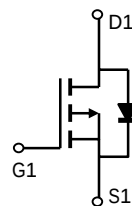
n-channel	p-channel
$V_{DS} (V) = 30V$	-30V
$I_D = 6.9A (V_{GS}=10V)$	-5.4A ($V_{GS} = -10V$)
$R_{DS(ON)}$	$R_{DS(ON)}$
$< 28m\Omega (V_{GS}=10V)$	$< 45m\Omega (V_{GS} = -10V)$
$< 42m\Omega (V_{GS}=4.5V)$	$< 75m\Omega (V_{GS} = -4.5V)$



SOIC-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current ^A	$T_A=25^\circ C$	6.9	-5.4	A
	$T_A=70^\circ C$	5.8	-4.6	
Pulsed Drain Current ^B	I_{DM}	30	-20	
Power Dissipation	$T_A=25^\circ C$	2	2	W
	$T_A=70^\circ C$	1.44	1.44	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	n-ch	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		n-ch	74	110	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	n-ch	35	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		p-ch	74	110	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	p-ch	35	40	$^\circ C/W$

N-CHANNEL: Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C		0.004	1	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.86	3	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =6.9A		22.5	28	mΩ
		T _J =125°C		31.3	38	
		V _{GS} =4.5V, I _D =5.0A		34.5	42	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =6.9A	10	15.4		S
V _{SD}	Diode Forward Voltage	I _S =1A		0.76	1	V
I _S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		680	820	pF
C _{oss}	Output Capacitance			102		pF
C _{rss}	Reverse Transfer Capacitance			77		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3	4.5	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =6.9A		13.84	17	nC
Q _g (4.5V)	Total Gate Charge			6.74	8.1	nC
Q _{gs}	Gate Source Charge			1.82		nC
Q _{gd}	Gate Drain Charge			3.2		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =2.2Ω, R _{GEN} =3Ω		4.6		ns
t _r	Turn-On Rise Time			4.1		ns
t _{D(off)}	Turn-Off DelayTime			20.6		ns
t _f	Turn-Off Fall Time			5.2		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =6.9A, dI/dt=100A/μs		16.5	20	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =6.9A, dI/dt=100A/μs		7.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t₁₀₀ ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

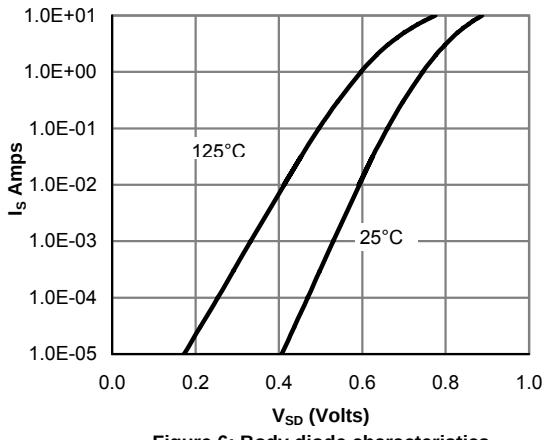
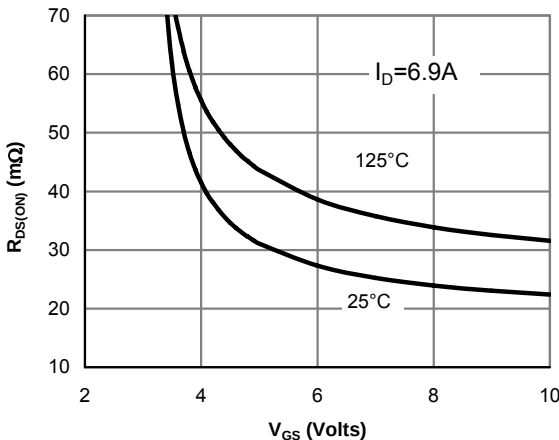
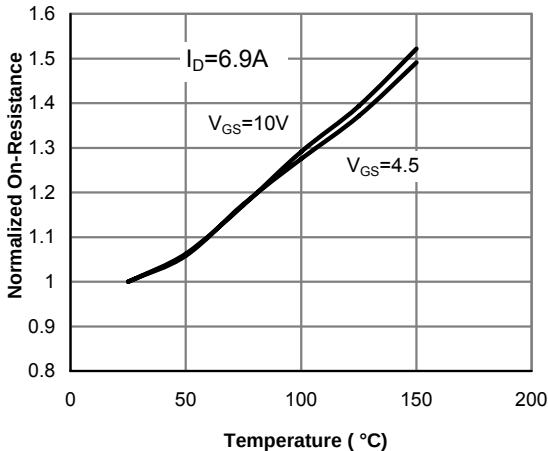
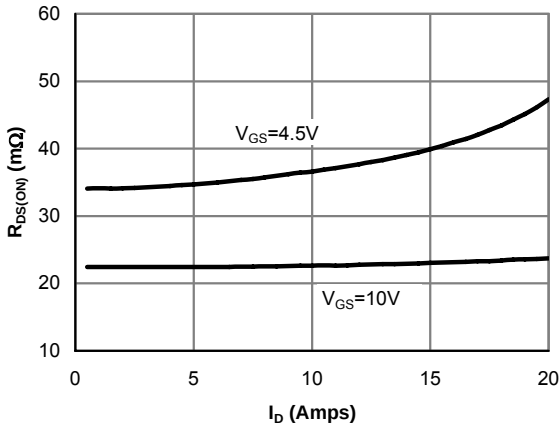
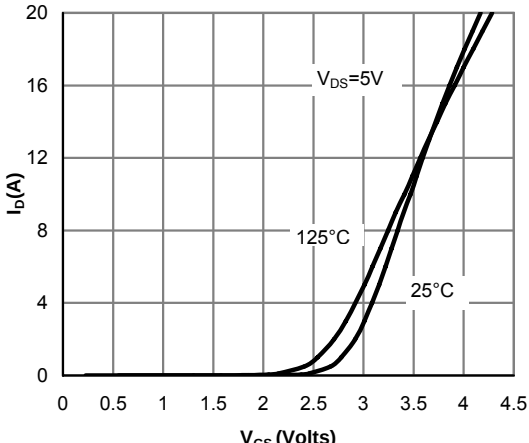
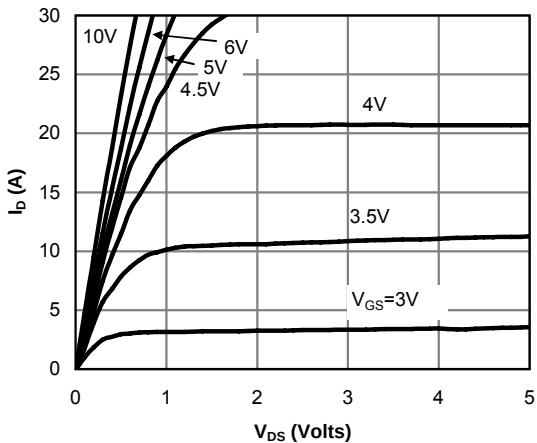
D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 0: Apr. 2006

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N-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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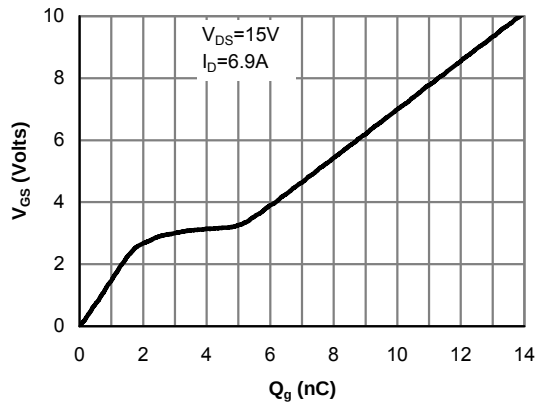


Figure 7: Gate-Charge characteristics

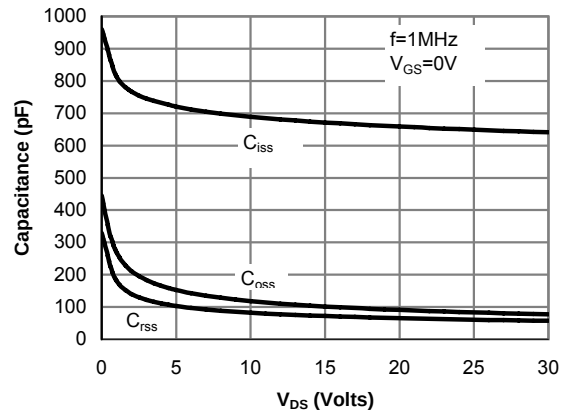


Figure 8: Capacitance Characteristics

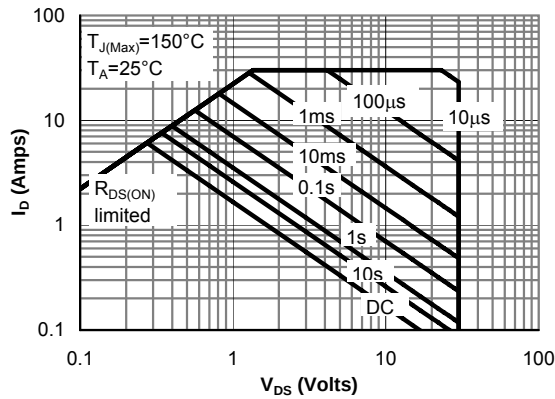


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

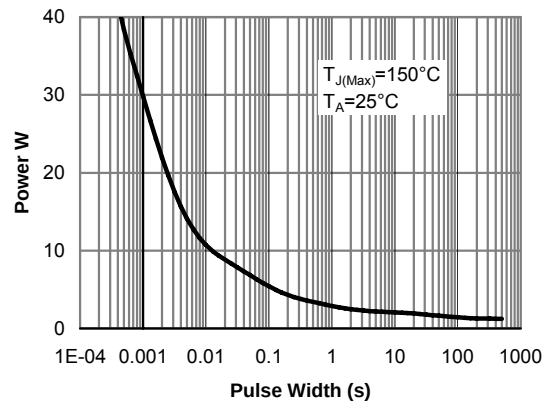


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

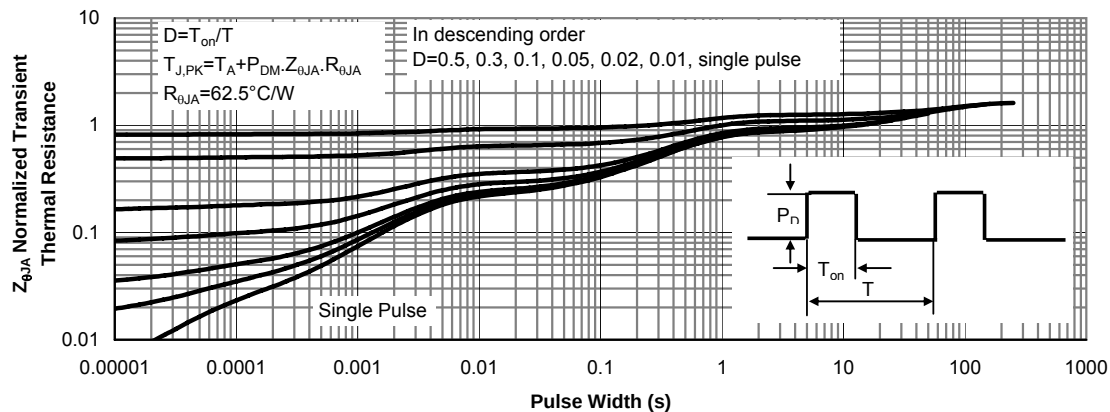


Figure 11: Normalized Maximum Transient Thermal Impedance

P-CHANNEL: Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-1	-1.98	-3	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-5.4A T _J =125°C		35 49	45 64	mΩ
		V _{GS} =-4.5V, I _D =-4A		58	75	
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-5.4A	6	8.6		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.78	-1	V
I _S	Maximum Body-Diode Continuous Current				-2.8	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		700	900	pF
C _{oss}	Output Capacitance			120		pF
C _{rss}	Reverse Transfer Capacitance			75		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		10	15	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge (10V)	V _{GS} =-10V, V _{DS} =-15V, I _D =-5.4A		14.7	19	nC
Q _g (4.5V)	Total Gate Charge (4.5V)			7.6	10	nC
Q _{gs}	Gate Source Charge			2		nC
Q _{gd}	Gate Drain Charge			3.8		nC
t _{D(on)}	Turn-On DelayTime			8.3		ns
t _r	Turn-On Rise Time	V _{GS} =-10V, V _{DS} =-15V, R _L =2.8Ω, R _{GEN} =3Ω		5		ns
t _{D(off)}	Turn-Off DelayTime			29		ns
t _f	Turn-Off Fall Time			14		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-5.4A, dI/dt=100A/μs		23.5	30	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-5.4A, dI/dt=100A/μs		13.4		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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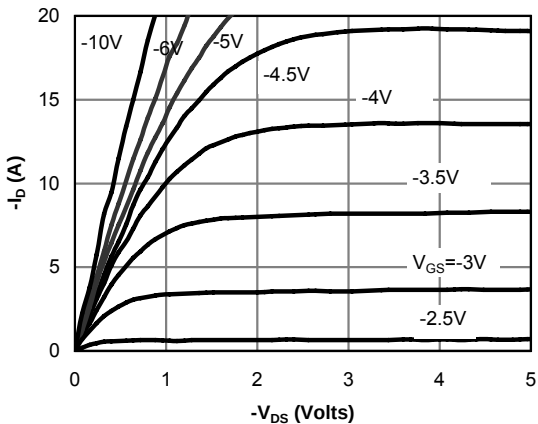


Figure 1: On-Region Characteristics

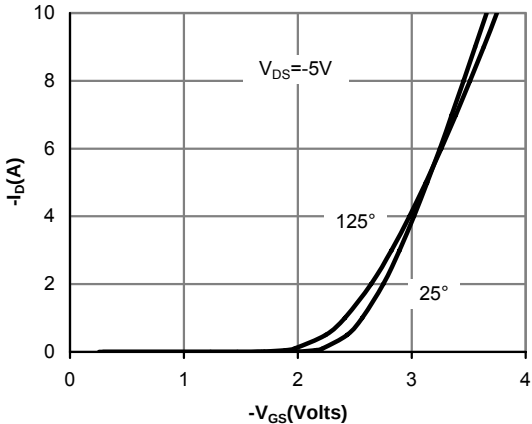


Figure 2: Transfer Characteristics

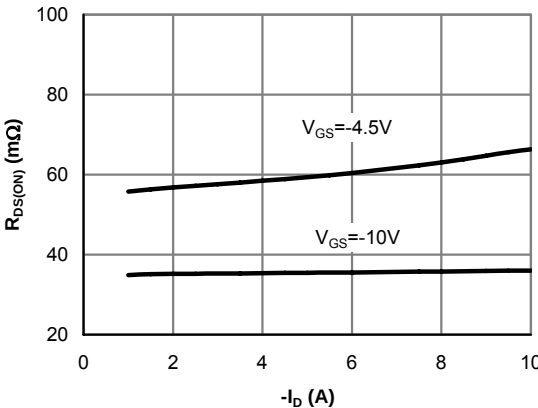


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

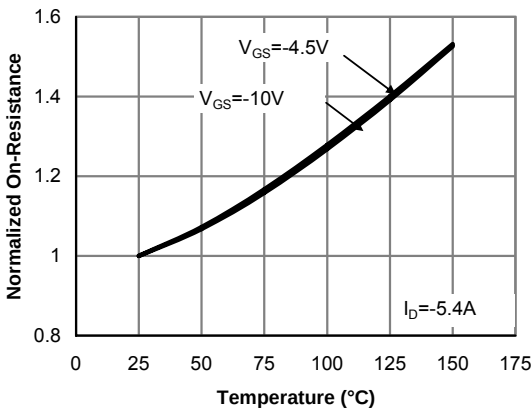


Figure 4: On-Resistance vs. Junction Temperature

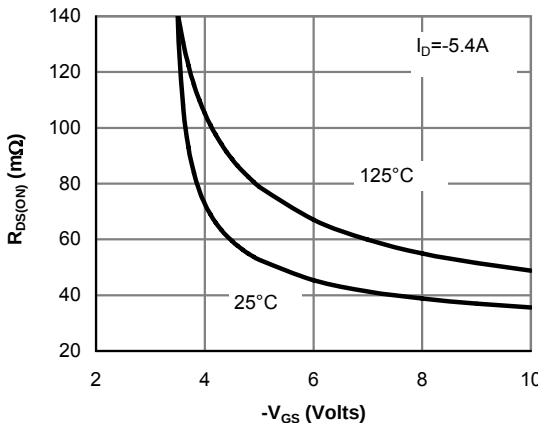


Figure 5: On-Resistance vs. Gate-Source Voltage

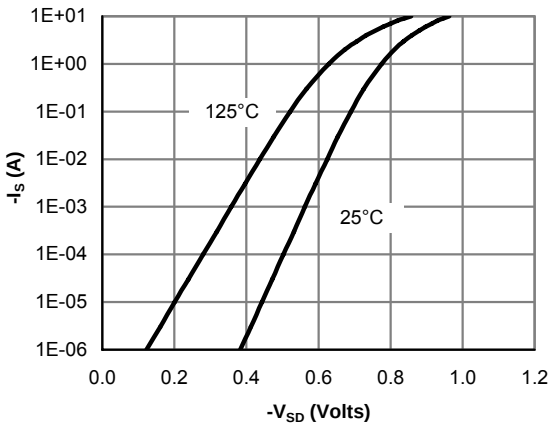


Figure 6: Body-Diode Characteristics

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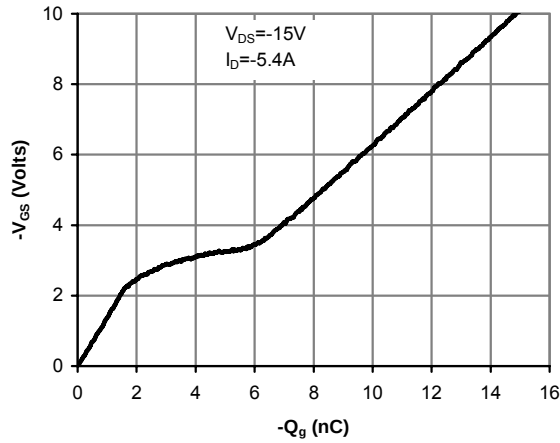


Figure 7: Gate-Charge Characteristics

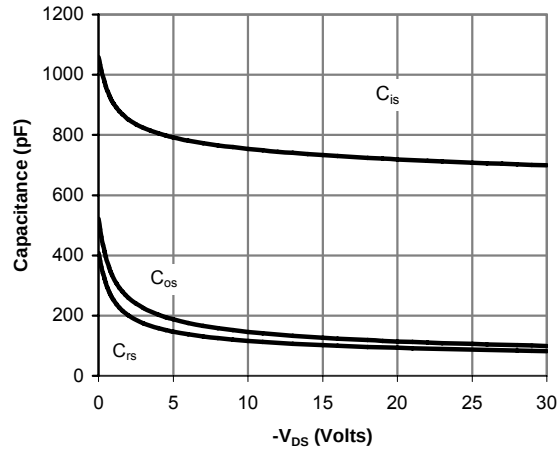


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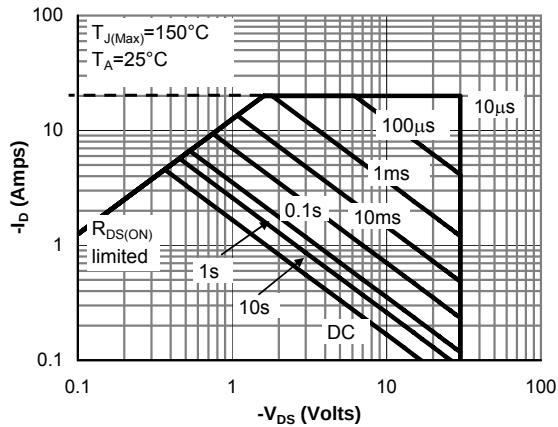


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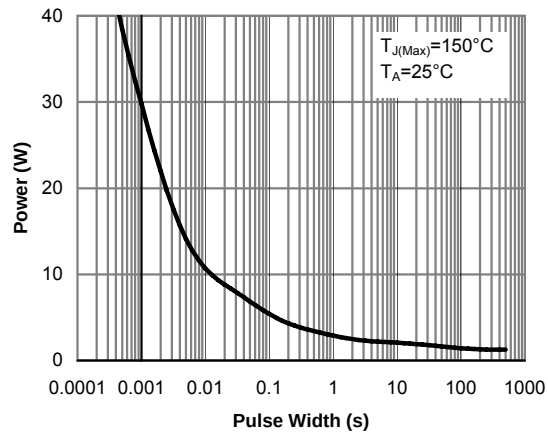


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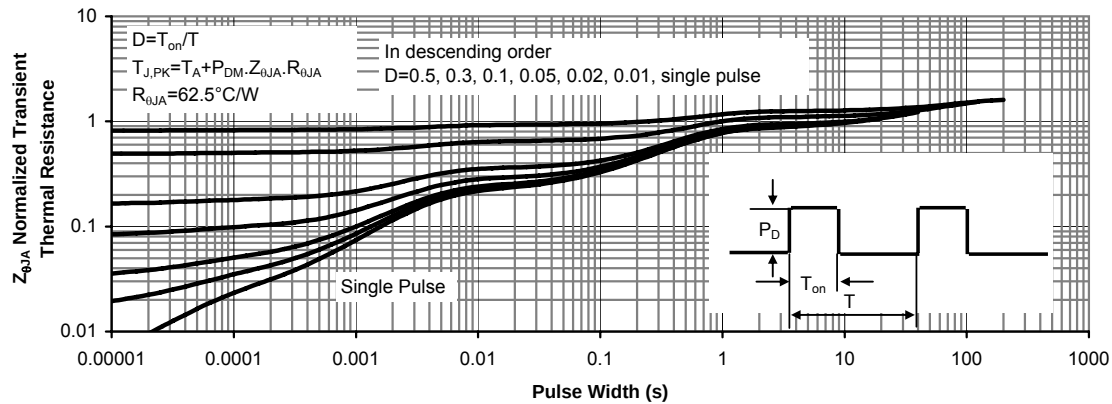


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